

Features

- ESD protect for 8 high-speed I/O channels
- Provide transient protection for each channel to IEC 61000-4-2 (ESD) $\pm 15\text{kV}$ (air), $\pm 8\text{kV}$ (contact) IEC 61000-4-5 (Lightning) 3A (8/20 μs)
- **For low operating voltage of 1.5V and below**
- **Ultra-low capacitance: 0.1pF typical**
- Fast turn-on and low clamping voltage
- Array of ESD rated diodes with internal equivalent TVS (Transient Voltage Suppression) diode
- Solid-state silicon-avalanche and active circuit triggering technology
- Simplified layout for high-speed differential signaling channels
- **Green part**

Applications

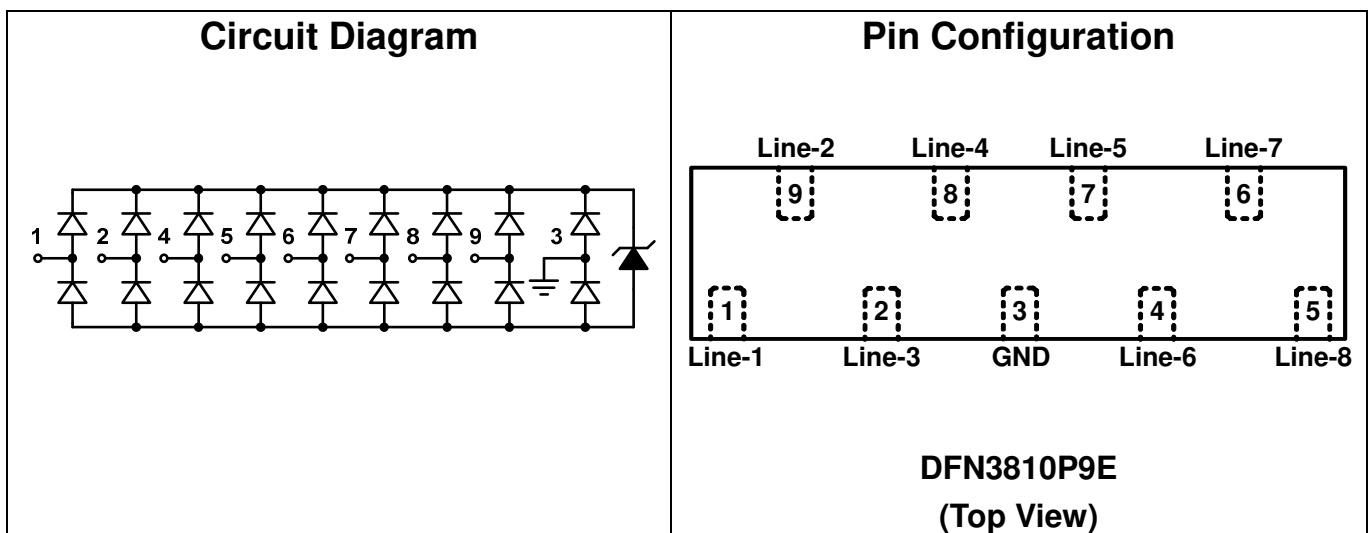
- V-by-One interface
- LVDS Interface
- USB 3.0 and USB 3.1 interfaces
- DisplayPort interface
- SATA and eSATA interfaces

Description

AZ111S-08F is a design which includes ESD rated diode arrays to protect high speed data interfaces. The AZ111S-08F has been specifically designed to protect sensitive components which are connected to data and transmission lines from over-voltage caused by Electrostatic Discharging (ESD).

AZ111S-08F is a unique design which includes ESD rated, ultra-low capacitance steering diodes and a unique design of clamping cell which is an equivalent TVS diode in a single package. During transient conditions, the steering diodes direct the transient to the ground line. The internal unique design of clamping cell prevents over-voltage on the I/O line, protecting any downstream components.

AZ111S-08F may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 ($\pm 15\text{kV}$ air, $\pm 8\text{kV}$ contact discharge).





SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)			
PARAMETER	SYMBOL	RATING	UNIT
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	3	A
Operating Voltage (I/O pin-GND)	V_{DC}	± 1.65	V
ESD per IEC 61000-4-2 (Air)	V_{ESD-1}	± 15	kV
ESD per IEC 61000-4-2 (Contact)	V_{ESD-2}	± 8	
Lead Soldering Temperature	T_{SOL}	260 (10 sec.)	$^\circ\text{C}$
Operating Temperature	T_{OP}	-55 to +125	$^\circ\text{C}$
Storage Temperature	T_{STO}	-55 to +150	$^\circ\text{C}$

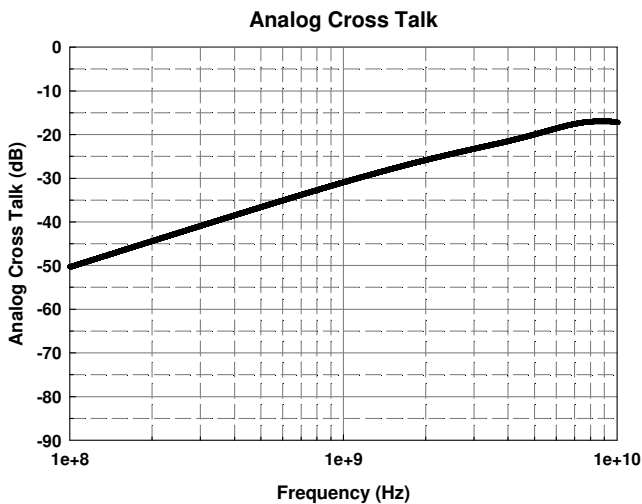
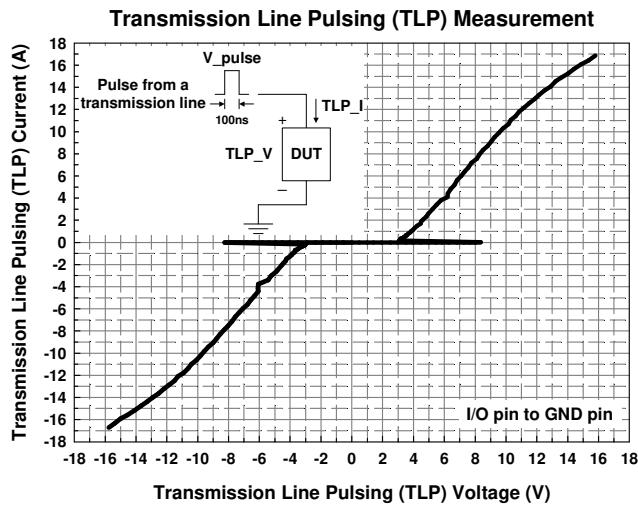
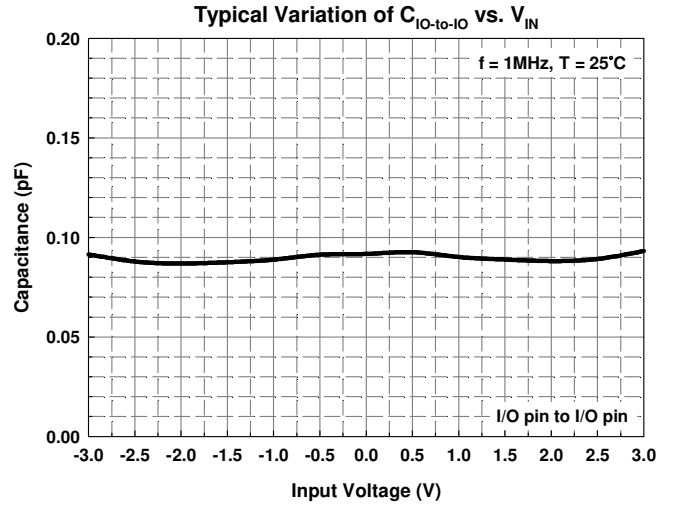
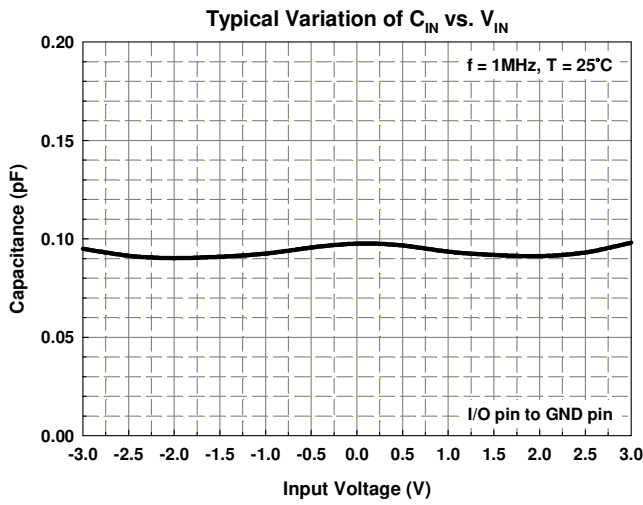
ELECTRICAL CHARACTERISTICS						
PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Reverse Stand-Off Voltage	V_{RWM}	Any I/O pin to GND, $T = 25^\circ\text{C}$.			1.5	V
Reverse Leakage Current	$I_{CH-Leak}$	$V_{RWM} = 1.5\text{V}$, $T = 25^\circ\text{C}$, any I/O pin to GND.			0.5	μA
Reverse Breakdown Voltage	V_{BV}	$I_{BV} = 1\text{mA}$, $T = 25^\circ\text{C}$, any I/O pin to GND.	4.5			V
ESD Clamping Voltage (Note 1)	V_{CL-ESD}	IEC 61000-4-2 +8kV ($I_{TLP} = 16\text{A}$), contact mode, any I/O pin to GND, $T = 25^\circ\text{C}$.		15		V
ESD Dynamic Turn-on Resistance	$R_{dynamic}$	IEC 61000-4-2, 0~+8kV, contact mode, any I/O pin to GND, $T = 25^\circ\text{C}$.		0.7		Ω
Channel Input Capacitance	C_{IN}	$V_{pin-3} = 0\text{V}$, $V_{IN} = 0\text{V}$, $f = 1\text{MHz}$, $T = 25^\circ\text{C}$, any I/O pin to GND.		0.10	0.15	pF
Channel to Channel Input Capacitance	C_{CROSS}	$V_{pin-3} = 0\text{V}$, $V_{IN} = 0\text{V}$, $f = 1\text{MHz}$, $T = 25^\circ\text{C}$, between I/O pins.		0.10	0.15	pF

Note 1: ESD Clamping Voltage was measured by Transmission Line Pulsing (TLP) System.

TLP conditions: $Z_0 = 50\Omega$, $t_p = 100\text{ns}$, $t_r = 1\text{ns}$.



Typical Characteristics





Application Information

The AZ111S-08F is designed to protect 8 high-speed data lines from transient over-voltage (such as ESD stress pulse). The device connection of AZ111S-08F is shown in the Fig. 1. In Fig. 1, the 8 protected high-speed data lines are connected to the ESD protection pins (pin1, pin2, pin4, pin5, pin6, pin7, pin8, and pin9) of AZ111S-08F. The AZ111S-08F is designed for

allowing the traces to run straight through the device to simplify the PCB layout. The ground pin (pin3) of AZ111S-08F is a negative reference pin. This pin should be directly connected to the GND rail of PCB. To get minimum parasitic inductance, the path length should keep as short as possible.

AZ111S-08F can provide ESD protection for 8 I/O signal lines simultaneously. If the number of I/O signal lines is less than 8, the unused I/O pins can be simply left as NC pins.

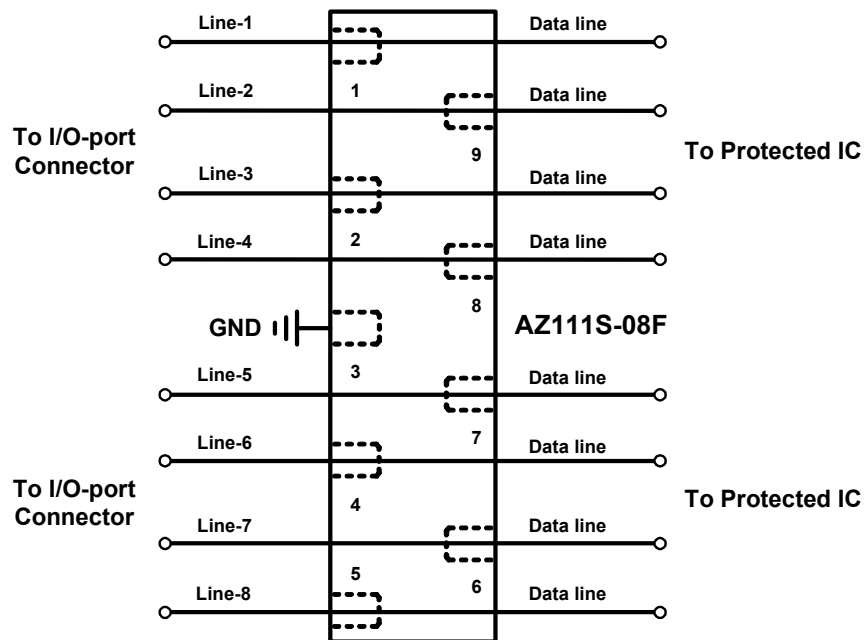


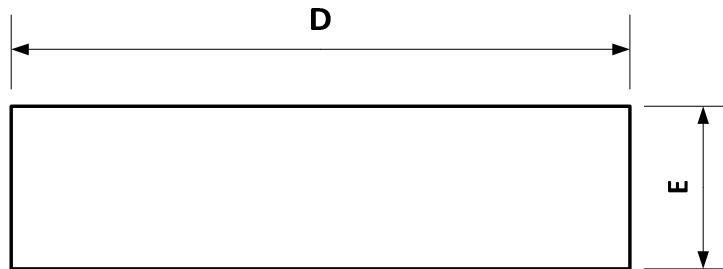
Fig. 1 Data lines connection of AZ111S-08F.

Mechanical Details

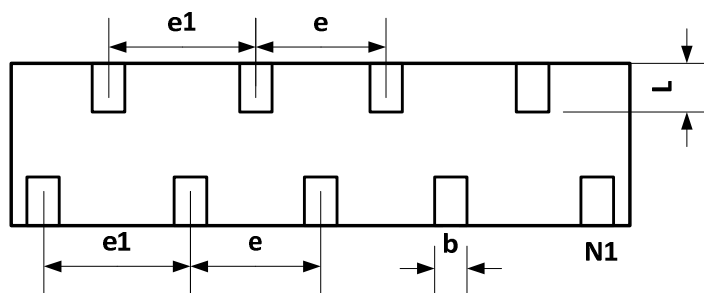
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PACKAGE DIAGRAMS AND DIMENSIONS

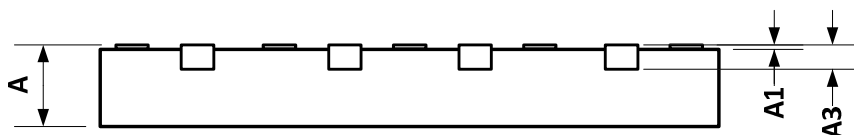
TOP VIEW



BOTTOM VIEW

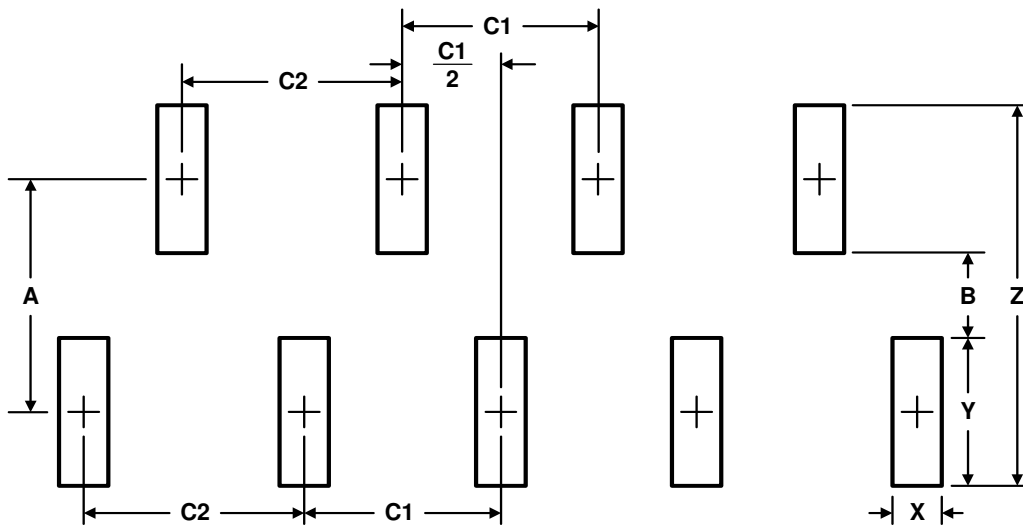


SIDE VIEW



SYMBOL	MILLIMETERS	
	MIN.	MAX.
A	0.45	0.55
A1	0.00	0.05
A3	0.15 REF.	
D	3.70	3.90
E	0.90	1.10
b	0.15	0.25
e	0.80 TYP.	
e1	0.90 TYP.	
L	0.20	0.40

LAND LAYOUT

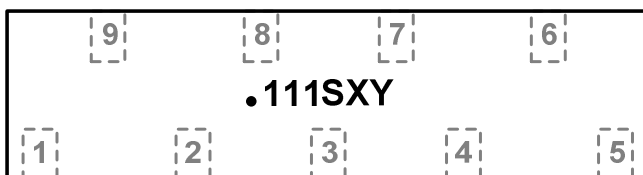


Notes:

This LAND LAYOUT is for reference purposes only. Please consult your manufacturing partners to ensure your company's PCB design guidelines are met.

Dimensions	
Index	Millimeters
A	0.95
B	0.35
C1	0.80
C2	0.90
X	0.20
Y	0.60
Z	1.55

MARKING CODE



111S=Device Code

X=Date Code

Y=Control Code

Part Number	Marking Code
AZ111S-08F.R7G (Green Part)	111SXY

Note. Green means Pb-free, RoHS, and Halogen free compliant.



Ordering Information

PN#	Material	Type	Real Size	MOQ	MOQ / internal box	MOQ / carton
AZ111S-08F.R7G	Green	T/R	7 inch	3,000/reel	3 reels = 9,000/box	6 boxes = 54,000/carton

Revision History

Revision	Modification Description
Revision 2019/01/14	Formal release.